

## **KSC838**

## FM Radio RF AMP, MIX, CONV, OSC, IF AMP

- High Current Gain Bandwidth Product : f<sub>T</sub>=250MHz (TYP.)
- Suffix "-C" means Center Collector (1. Emitter 2. Collector 3. Base)



## **NPN Epitaxial Silicon Transistor**

## **Absolute Maximum Ratings** $T_a$ =25°C unless otherwise noted

Symbol	Parameter	Value	Units
V <sub>CBO</sub>	Collector-Base Voltage	35	V
V <sub>CEO</sub>	Collector-Emitter Voltage	30	V
V <sub>EBO</sub>	Emitter-Base Voltage	4	V
I <sub>C</sub>	Collector Current	30	mA
P <sub>C</sub>	Collector Power Dissipation	250	mW
TJ	Junction Temperature	150	°C
T <sub>STG</sub>	Storage Temperature	-55 ~ 150	°C

## Electrical Characteristics T<sub>a</sub>=25°C unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Тур.	Max.	Units
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	$I_{C}=100\mu A, I_{E}=0$	35			V
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> =5mA, I <sub>B</sub> =0	30			V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> =10μA, I <sub>C</sub> =0	4			V
I <sub>CBO</sub>	Collector Cut-off Current	$V_{CB}$ =30V, $I_{E}$ =0			0.1	μΑ
I <sub>EBO</sub>	Emitter Cut-off Current	$V_{EB}=4V$ , $I_{C}=0$			0.1	μΑ
h <sub>FE</sub>	DC Current Gain	V <sub>CE</sub> =12V, I <sub>C</sub> =2mA	40		240	
V <sub>BE</sub> (on)	Base-Emitter On Voltage	V <sub>CE</sub> =6V, I <sub>C</sub> =1mA	0.65	0.70	0.75	V
V <sub>CE</sub> (sat)	Collector-Emitter Saturation Voltage	I <sub>C</sub> =10mA, I <sub>B</sub> =1mA		0.1	0.4	V
f <sub>T</sub>	Current Gain Bandwidth Product	V <sub>CE</sub> =10V, I <sub>C</sub> =1mA	100	250		MHz
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> =10V, I <sub>E</sub> =0, f=1MHz		2.0	3.2	pF

## **h**<sub>FE</sub> Classification

Classification	R	0	Y
h <sub>FE</sub>	40 ~ 80	70 ~ 140	120 ~ 240

## **Typical Characteristics**

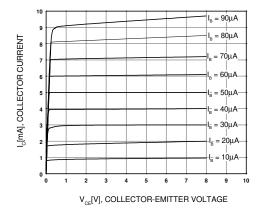


Figure 1. Static Characteristic

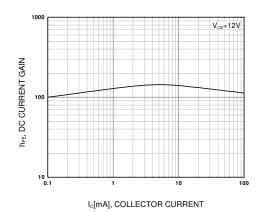


Figure 2. DC current Gain

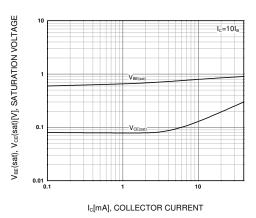


Figure 3. Base-Emitter Saturation Voltage Collector-Emitter Saturation Voltage

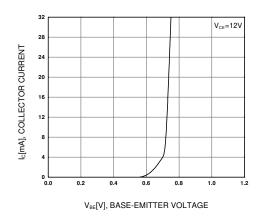


Figure 4. Base-Emitter On Voltage

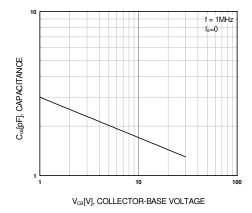


Figure 5. Collector Output Capacitance

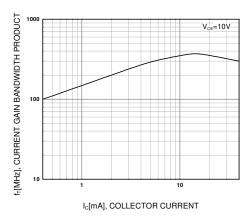
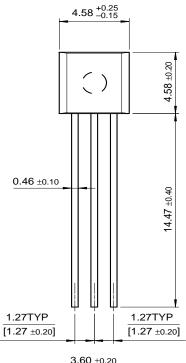


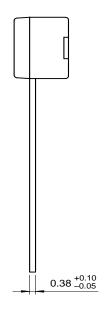
Figure 6. Current Gain Bandwidth Product

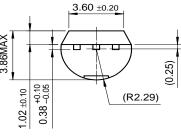
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# **Package Demensions**

TO-92







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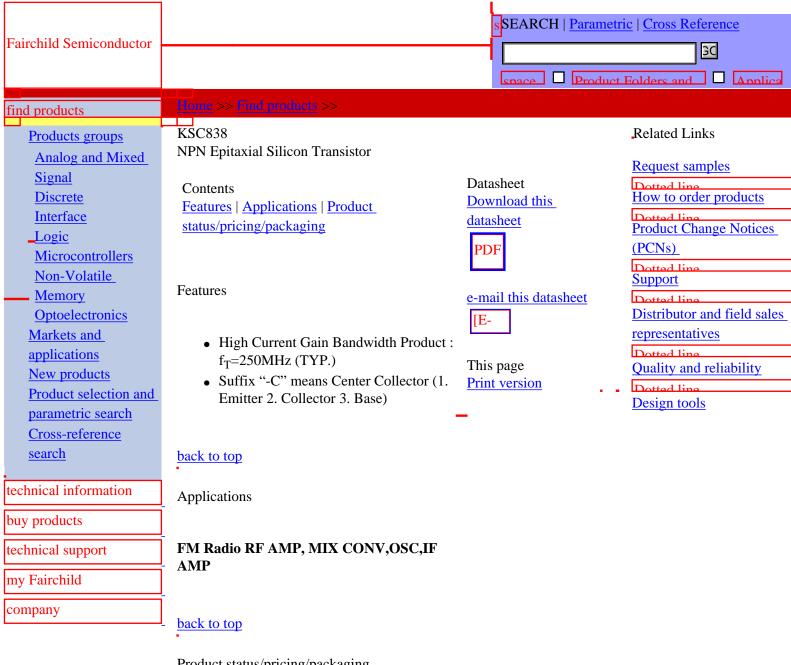
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Product status/pricing/packaging

Product	Product status	Pricing*	Package type	Leads	Packing method
KSC838COTA	Full Production	\$0.045	<u>TO-92</u>	3	TAPE REEL
KSC838CYTA	Full Production	\$0.045	<u>TO-92</u>	3	TAPE REEL
KSC838YBU	Full Production	\$0.045	<u>TO-92</u>	3	BULK
KSC838OBU	Full Production	\$0.045	<u>TO-92</u>	3	BULK
KSC838YTA	Full Production	\$0.045	<u>TO-92</u>	3	TAPE REEL
KSC838CYBU	Full Production	\$0.045	<u>TO-92</u>	3	BULK
KSC838OTA	Full Production	\$0.045	<u>TO-92</u>	3	TAPE REEL
KSC838COBU	Full Production	\$0.045	TO-92	3	BULK

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